36 V Bipolar Array
K4R

Special Features:

- improved V_{BE}-matching
- Trimmcells
- SiCr Resistors
- 40V-NPN-Transistors
- low leakage PNP-Transistors

Die Size	app. 2.5 x 2.0 mm²
V_{max}	36 V
Bonding Pads	20
40 V 40 mA NPN Transistor	13
20 mA NPN Transistor	2
10 mA NPN Transistor	3
5 mA NPN Transistor	70
5 mA NPN Transistor (trimmcell)	9
1 mA PNP Transistor lateral	36
1 mA PNP Transistor lateral (low leakage)	2

1.2 kΩ Resistor (base diffused)	14
0.6 kΩ Resistor (base diffused)	14
12 kΩ Resistor (SiCr)	124
6 kΩ Resistor (SiCr)	124
Crossunder	66
18 pF Capacitor	1
19 pF Capacitor	1
Total Resistance (diffused)	25 kΩ
Total Resistance (SiCr)	2.2 MΩ
Total Capacitance	37 pF